

Form PTO-1449
(Rev. 8-83)

U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-2149

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hisashi OHTANI et al.

Filing Date: June 14, 2000

Group: 2824

U.S. PATENT DOCUMENTS

| Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date (if appropriate) |
|------------------|-----------------|----------|----------------|-------|----------|------------------------------|
| CN | 3,856,565 | 12/24/74 | Arnold | | | |
| CN | 5,248,630 | 09/28/93 | Serikawa et al | | | |
| CN | 5,252,502 | 10/12/93 | Havemann | | | |
| CN | 5,395,804 | 03/07/95 | Ueda | | | |
| CN | 5,550,070 | 8/27/96 | Funai et al. | | | |
| CN | 5,147,826 | 9/15/92 | Liu et al. | | | |
| CN | 5,275,851 | 1/4/94 | Fonash | | | |
| CN | 5,075,259 | 12/24/91 | Moran | | | |
| CN | 5,488,000 | 1/30/96 | Zhang et al. | | | |
| CN | 5,403,772 | 4/4/95 | Zhang et al. | | | |

JC542 U.S. PTO
09/593765
06/14/00

FOREIGN PATENT DOCUMENTS

| | Document Number | Date | Country | Class | Subclass | Translation Yes No |
|----|--------------------|---------------------|------------------|-------|----------|-----------------------|
| | 3-25540 | 01/30/91 | Japan | | | Abstract |
| CN | 3-280420 | 12/11/91 | Japan | | | Full |

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | | |
|----|--|---|
| CN | | Wolf, Stanley, "Silicon Processing for the VLSI Era Volume 2; Process Integration", Lattice Press, 1990, pages 256-257. |
| CN | | Wolf et al., "Silicon Processing for the VLSI Era Volume 1; Process Technology", Lattice Press, 1986, pages 215-216. |
| CN | | C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon", 1991. |
| CN | | A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals", Akademikian Lavrentev Prospekt 13, 630090 Novosibirsk 90, USSR, pp. 635-640, 1986. |
| CN | | T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films", Solid State Communications, Vol. 85, No. 11, pp. 921-924, 1993. |
| CN | | R. Kakkad, J. Smith, W.S. Lau, S.J. Fonash, "Crystallized Si Films By Low-Temperature Rapid Thermal Annealing of Amorphous Silicon", J. Appl. Phys. 65 (5), March 1, 1989, 1989 American Institute of Physics, pp. 2069-2072. |

Examiner

Date Considered

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-2149

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hisashi Ohtani et al.

Filing Date: June 14, 2000

Group: 2824

U.S. PATENT DOCUMENTS

| Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date (if appropriate) |
|------------------|-----------------|----------|-----------------|-------|----------|------------------------------|
| CN | 5,403,772 | 04/04/95 | Zhang et al | | | |
| CN | 5,426,064 | 06/20/95 | Zhang et al | | | |
| CN | 5,481,121 | 01/02/96 | Zhang et al | | | |
| CN | 5,488,000 | 01/30/96 | Zhang et al | | | |
| CN | 5,492,843 | 02/20/96 | Adachi et al | | | |
| CN | 5,501,989 | 03/26/96 | Takayama et al | | | |
| CN | 5,508,533 | 04/16/96 | Takemura | | | |
| CN | 5,529,937 | 06/25/96 | Zhang et al | | | |
| CN | 5,534,716 | 07/09/96 | Takemura | | | |
| CN | 5,543,352 | 08/06/96 | Ohtani et al | | | |
| CN | 5,563,426 | 10/08/96 | Zhang et al | | | |
| CN | 5,569,610 | 10/29/96 | Zhang et al | | | |
| CN | 5,569,936 | 10/29/96 | Zhang et al | | | |
| CN | 5,580,792 | 12/03/96 | Zhang et al | | | |
| CN | 5,585,291 | 12/17/96 | Ohtani et al | | | |
| CN | 5,589,694 | 12/31/96 | Takayama et al | | | |
| CN | 5,595,923 | 01/21/97 | Zhang et al. | | | |
| CN | 5,595,944 | 01/21/97 | Zhang et al. | | | |
| CN | 5,604,360 | 02/18/97 | Zhang et al. | | | |
| CN | 5,605,846 | 02/25/97 | Ohtani et al. | | | |
| CN | 5,606,179 | 02/25/97 | Yamazaki et al. | | | |
| CN | 5,608,232 | 03/04/97 | Yamazaki et al. | | | |
| CN | 5,612,250 | 03/18/97 | Ohtani et al. | | | |
| CN | 5,614,426 | 03/25/97 | Funada et al. | | | |
| CN | 5,614,733 | 03/25/97 | Zhang et al. | | | |
| CN | 5,616,506 | 04/01/97 | Takemura | | | |

Examiner

Chy C

Date Considered

8-2-01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-2149

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hisashi OHTANI et al.

Filing Date: June 14, 2000

Group: 2824

U.S. PATENT DOCUMENTS

| Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date (if appropriate) |
|------------------|-----------------|----------|----------------|-------|----------|------------------------------|
| cn | 5,620,910 | 04/15/97 | Teramoto | | | |
| cn | 5,621,224 | 04/15/97 | Yamazaki et al | | | |
| cn | 5,624,851 | 04/29/97 | Takayama et al | | | |
| cn | 5,637,515 | 06/10/97 | Takemura | | | |
| cn | 5,639,698 | 06/17/97 | Yamazaki et al | | | |
| cn | 5,643,826 | 07/01/97 | Ohtani et al | | | |
| cn | 5,646,424 | 07/08/97 | Zhang et al | | | |
| cn | 5,654,203 | 08/05/97 | Ohtani et al | | | |
| cn | 5,656,825 | 08/12/97 | Kusumoto et al | | | |
| cn | 5,663,077 | 09/02/97 | Adachi et al | | | |
| cn | 5,677,549 | 10/14/97 | Takayama et al | | | |
| cn | 5,696,386 | 12/09/97 | Yamazaki | | | |
| cn | 5,696,388 | 12/09/97 | Funada et al | | | |
| cn | 5,700,333 | 12/23/97 | Yamazaki et al | | | |
| cn | 5,705,829 | 01/06/98 | Miyanaga et al | | | |
| cn | 5,712,191 | 01/27/98 | Nakajima et al | | | |
| cn | 5,756,364 | 05/26/98 | Tanaka et al | | | |

FOREIGN PATENT DOCUMENTS

| Document Number | Date | Country | Class | Subclass | Translation Yes No |
|-----------------|------|---------|-------|----------|-----------------------|
| | | | | | |

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | |
|----|--|
| cn | G. Liu, S.J. Fonash, "Polycrystalline ilicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low Temperature Processing", Appl. Phys. Lett. 62 (20), May 17, 1993, 1993 American Institute of Physics, pp. 2554-2556. |
| cn | G. Liu and S.J. Fonash, "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing", Appl. Phys. Lett. 55 (7), August 14, 1989, 1989 American Institute of Physics, pp. 660-662. |
| cn | R. Kakkad, G. Liu, S.J. Fonash, "Low Temperature Selective Crystallization of Amorphous Silicon", Journal of Non-Crystalline Solids, Volume 115, (1989), pp. 66-68. |

Examiner

Date Considered

8-2-01

*EXAMINER: Initial if citation considered, wh ther or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-2149

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Hisashi OHTANI et al.

Filing Date: June 14, 2000

Group: 2824

U.S. PATENT DOCUMENTS

| Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date (if appropriate) |
|------------------|-----------------|----------|----------------|-------|----------|------------------------------|
| cn | 5,492,843 | 02/20/96 | Adachi et al. | 437 | 21 | |
| cn | 5,481,121 | 01/02/96 | Zhang et al. | 257 | 64 | |
| cn | 5,244,836 | 09/14/93 | Lim | 437 | 192 | |
| cn | 3,783,049 | 01/01/74 | Sandera | 437 | 159 | |
| cn | 4,959,247 | 09/25/90 | Moser et al. | 427 | 126.5 | |
| cn | 5,358,907 | 10/25/94 | Wong | 437 | 230 | |
| cn | 5,480,811 | 01/02/96 | Chiang et al. | 437 | 159 | |
| cn | 4,379,020 | 04/05/96 | Glaeser et al. | | | |
| cn | 5,531,182 | 07/02/96 | Yonehara | 437 | 973 | |
| cn | 4,068,020 | 01/10/78 | Reuschel | 437 | 88 | |
| cn | 5,529,937 | 06/25/96 | Zhang et al. | | | |

FOREIGN PATENT DOCUMENTS

| | Document Number | Date | Country | Class | Subclass | Translation Yes No |
|----|-----------------|----------|---------|-------|----------|-----------------------|
| cn | 2-140915 | 05/30/90 | Japan | | | Full |
| cn | 1-206632 | 08/18/89 | Japan | | | Abstract |

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

| | |
|----|---|
| cn | F. Spaepen et al., Crucial Issues in Semiconductor Materials & Processing Technologies., S. Coffa et al. (eds), Kluwer (1992) 483-498. |
| | Y. Kawazu et al., Jpn. J. Appl. Phys. 29(4) (1990) 729-738, "Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon." |
| cn | S. Caune et al., Applied Surface Sciences 36 (1989) 597-604 "Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals" (Abstract) |
| | T.B. Suresh et al., Thin Solid Films, 252 (1994) 78-81 "Electroless Plated Nickel Contacts to Hydrogenated Amorphous Silicon" |
| cn | F. Oki et al., Jpn. J. Appl. Phys., 8(1969) 1056, "Effect of Deposited Metals on the Crystallization Temperature of Amorphous Germanium Film" |

Examiner

Date Considered

8-02-01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Atty Docket 0756-2149

Serial No. Unassigned

INFORMATION DISCLOSURE STATEMENT

Applicants: Hisashi OHTANI et al.

Filing Date: June 14, 2000

Group Art Unit:

FOREIGN PATENT DOCUMENTS

| Examiner Initial | Document Number | Date | Country | Class | Subclass | Translation | |
|---------------------|-----------------|------------|---------|-------|----------|-------------|----|
| | | | | | | Yes | No |
| cn | 3-22540 | 01/30/1991 | Japan | | | Full | |

RECEIVED
DEC - 7 2000
TC 2800 MAIL ROOM

Examiner

Date Considered

8-2-01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.